

ABSTRACT OF THE DISCLOSURE

Nonvolatile memory wordlines (160) are formed as sidewall spacers on sidewalls of control gate structures (280). Each control gate structure may contain floating and control gates (120, 140), or some other elements. Pedestals (340) are formed adjacent to
5 the control gate structures before the conductive layer (160) for the wordlines is deposited. The pedestals will facilitate formation of the contact openings (330.1) that will be etched in an overlying dielectric (310) to form contacts to the wordlines. The pedestals can be dummy structures. A pedestal can physically contact two wordlines.